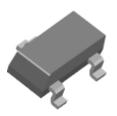
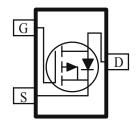
P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCTSUMMARY					
V _{DS} (V)	r _{DS(on)} (OHM)	$I_{D}(A)$			
-20	$0.079 @V_{CS} = -4.5V$	-1.7			
-20	$0.110 @V_{CS} = -2.5V$	-1.5			

- Low $r_{DS(\text{on})}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SC70-3 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter			Symbol Maximum		
Drain-Source Voltage			-20	V	
Cate-Source Voltage			±8	V	
	T _A =25°C	т	-1.7		
Continuous Drain Current ^a	T _A =25°C T _A =70°C	TD	-1.4	Α	
Pulsed Drain Current ^b			-2.5		
Continuous Source Current (Diode Conduction) ^a		I_S	±0.28	Α	
D	T _A =25°C	D	0.34	W	
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	FD	0.22	. **	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
N	$t \le 5 \sec$	D	375	0000		
Maximum Junction-to-Ambient ^a	Steady-State	R_{THJA}	430			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)								
Parameter	C11	Trut Con Pt.	Limits			TI		
rarameter	Symbol	Symbol Test Conditions		Тур	Max	Unit		
Static								
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.4			V		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \ V, \ V_{GS} = \pm 8 \ V$			±100	nA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	4		
Zero Gate Voltage Drain Current	¹ DSS	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ} \text{C}$			-10	uA		
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-5			Α		
Drain-Source On-Resistance ^A	r	$V_{GS} = -4.5 \text{ V}, I_D = -1.7 \text{ A}$			79	mΩ		
Drain-Source On-Resistance	$r_{\mathrm{DS(on)}}$	$V_{GS} = -2.5 \text{ V}, I_D = -1.5 \text{ A}$			110	insz		
Forward Tranconductance ^A	$g_{ m fs}$	$V_{DS} = -5 \text{ V}, I_D = -1.25 \text{ A}$		9		S		
Diode Forward Voltage	V_{SD}	$I_S = -0.46 \text{ A}, V_{GS} = 0 \text{ V}$		-0.65		V		
Dynamic ^b								
Total Gate Charge	Q_{g}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$		7.2				
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -1.7 \text{ A}$		1.7		пC		
Gate-Drain Charge	Q_{gd}	I _D 1. / A		1.5				
Turn-On Delay Time	$t_{d(on)}$			10				
Rise Time	$t_{\rm r}$	$V_{DD} = -10 \text{ V}, I_L = -1 \text{ A},$		9		na		
Turn-Off Delay Time	$t_{d(off)}$	V_{GEN} = -4.5 V, R_G = 6 Ω		27		ns		
Fall-Time	t_{f}			11				

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Repetitive rating, pulse width limited by junction temperature.

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Typical Electrical Characteristics

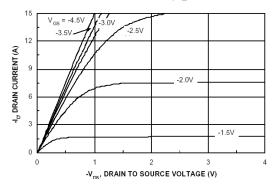


Figure 1. On-Region Characteristics

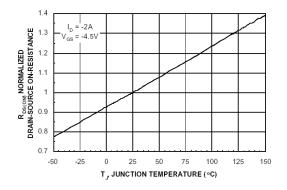


Figure 3. On-Resistance Variation with Temperature

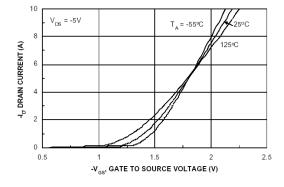


Figure 5. Transfer Characteristics

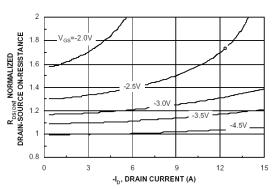


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

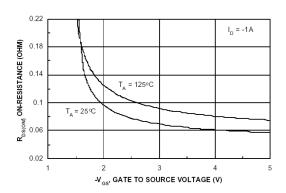


Figure 4. On-Resistance Variation with Gate to Source Voltage

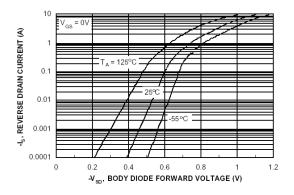


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Electrical Characteristics

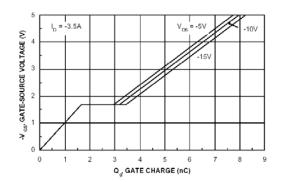


Figure 7. Gate Charge Characteristic

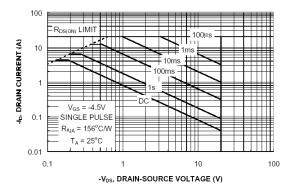


Figure 8. Capacitance Characteristic

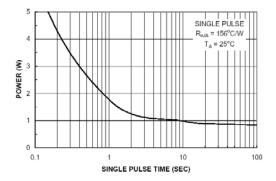


Figure 9. Maximum Safe Operating Area

Figure 10. Single Pulse Maximum Power
Dissipation



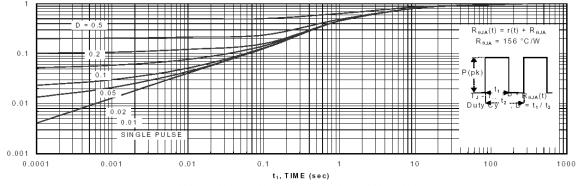
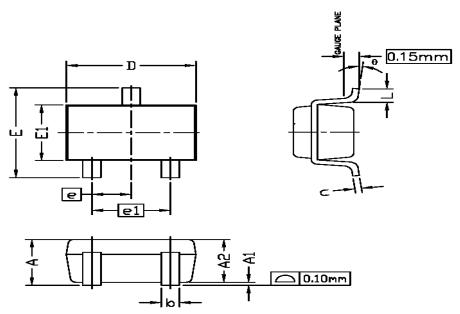


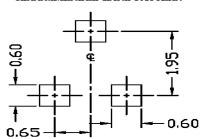
Figure 11. Transient Thermal Response Curve.

Package Information

SC70 PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



UN	IT:	mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIM	MI NI ENOIENE	CHES
SIMBULS	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.00		0.004
A2	0.7	0.9	1.00	0.028	0.035	0.039
ь	0.15		0.30	0.006		0.012
c	0.08		0.22	0.003		0.009
D	1.85	2.10	2,15	0.073	0.083	0.085
E	1.80	2.30	2.40	0.071	0.091	0.094
e		0.65 BSC		0.026 BSC		
el	1.30 BSC			0.051 BSC		
E 1	1.1	1.30	1.4	0.043	0.051	0.055
L	0.26	0.36	0.46	0.010	0.014	0.018
θ	0°	4°	80	0°	4°	80

NOTE

- 1. ALL DIMENSIONS ARE IN MILLMETERS.
- 2. DIMENSIONS ARE INCLUSIVE OF PLATING.
- 3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 3 MILS EACH.
- 4. DIE IS FACING UP FOR MOLD AND FACING DOWN FOR TRIM/FORM. ie: REVERSE TRIM/FORM.
- 5. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 6. CONTROLLING DIMENSION IS MILLIMETER.
- CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.